What Is Claimed Is:

1. A method to fabricate a semiconductor device comprising:

forming a nitride layer on an interlayer insulating layer;

forming a photoresist layer on the nitride layer;

forming a photoresist pattern from the photoresist layer;

etching the nitride layer using the photoresist pattern as a mask;

simultaneously etching the photoresist pattern and the interlayer insulating layer; and

setting an etch stop point as a point at which the photoresist pattern is removed by etching.

2. A method as defined in claim 1, wherein the nitride layer has a thickness of approximately 200-800 Å.

3. A method as defined in claim 1, wherein the photoresist pattern has a thickness of approximately 2500-3500 Å.

4. A method as defined in claim 1, further comprising, after the photoresist pattern is removed, over-etching the interlayer insulating layer using the nitride layer as a mask.

5. A method to fabricate a semiconductor device comprising:

forming a first mask layer on an etch target layer;

forming a second mask layer on the first mask layer;

forming a first mask pattern by selectively etching the second mask layer;

forming a second mask pattern by etching the first mask layer using the first mask pattern as a mask;

etching the first mask pattern and the etch target layer using the second mask pattern as a mask; and

setting an etch stop point as a point at which the first mask pattern is removed by etching.

6. A method as defined in claim 5, wherein the first mask layer and the etch target layer have a same etch rate.

7. A method as defined in claim 5, wherein the first mask layer and the etch target layer have a different etch rate.

8. A method as defined in claim 6, wherein a thickness of the first mask layer is determined by a desired etch depth in the etch target layer.

9. A method as defined in claim 8, wherein the first mask layer is made from a same material as the etch target layer.

10. A method to fabricate a semiconductor device comprising:

forming a nitride layer on an interlayer insulating layer;

forming a photoresist layer on the nitride layer;

forming a photoresist pattern from the photoresist layer;

etching the nitride layer using the photoresist pattern as a mask;

simultaneously etching the photoresist pattern and the interlayer insulating layer; and

setting an etch stop point as a point at which the nitride layer is exposed.

11. A method to fabricate a semiconductor device comprising:

forming a first mask layer on an etch target layer;

forming a second mask layer on the first mask layer;

forming a first mask pattern by selectively etching the second mask layer;

forming a second mask pattern by etching the first mask layer using the first mask pattern as a mask;

etching the first mask pattern and the etch target layer using the second mask pattern as a mask; and

setting an etch stop point as a point at which the second mask pattern is exposed.